TOSHIBA

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

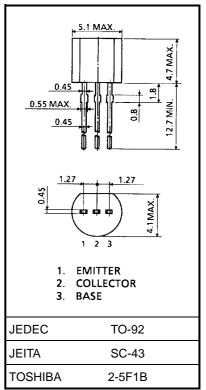
# 2SC3279

### Strobe Flash Applications Medium Power Amplifier Applications

- High DC current gain and excellent hFE linearity
  : hFE (1) = 140~600 (VCE = 1 V, IC = 0.5 A)
  : hFE (2) = 70 (min), 200 (typ.) (VCE = 1 V, IC = 2 A)
- Low saturation voltage:  $V_{CE}$  (sat) = 0.5 V (max) (IC = 2 A, IB = 50 mA)

#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	30	V	
Collector-emitter voltage		V <sub>CES</sub>	30	V	
		V <sub>CEO</sub>	10		
Emitter-base voltage		V <sub>EBO</sub>	6	V	
Collector current	DC	Ι <sub>C</sub>	2	A	
	Pulsed (Note 1)	I <sub>CP</sub>	5		
Base current		Ι <sub>Β</sub>	0.2	А	
Collector power dissipation		PC	750	mW	
Junction temperature		Тj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 0.21 g (typ.)

Note 1:	Pulse width = 10 ms	(max), dutv	cvcle = 30% (max)
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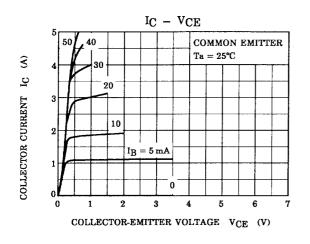
## **Electrical Characteristics (Ta = 25°C)**

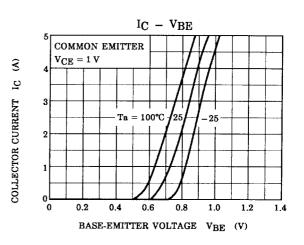
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$	_		0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 6 V, I_{C} = 0$	_	_	0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	10	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_{E} = 1 \text{ mA}, I_{C} = 0$	6	_		V
DC current gain	h <sub>FE (1)</sub> (Note 2)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 0.5 \text{ A}$	140	_	600	
	h <sub>FE (2)</sub>	$V_{CE} = 1 V, I_{C} = 2 A$	70	200		
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{C} = 2 \text{ A}, I_{B} = 50 \text{ mA}$	_	0.2	0.5	V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = 1 V, I_{C} = 2 A$	_	0.86	1.5	V
Transition frequency	fT	$V_{CE} = 1 \text{ V}, I_{C} = 0.5 \text{ A}$	_	150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		27		pF

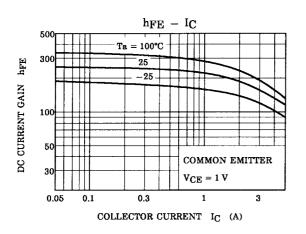
Note 2: hFE (1) classification L: 140~240, M: 200~330, N: 300~450, P: 420~600

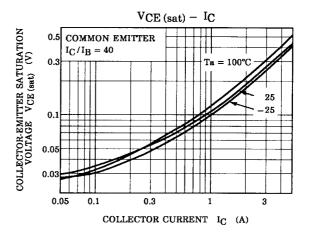
Unit: mm

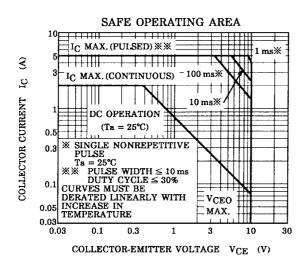
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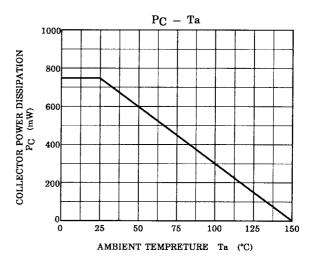












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